

Low Frequency Transistor (50V, 2A)

2SC4672

●Features

- 1) Low saturation voltage, typically $V_{CE(sat)} = 0.1V$ at $I_C/I_B = 1A/50mA$.
- 2) Excellent DC current gain characteristics.
- 3) Complements the 2SA1797.

●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	60	V
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V_{EBO}	6	V
Collector current	I_C	2	A (DC)
		5	A (Pulse) *
Collector power dissipation	P_C	0.5	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55~+150	°C

* Single pulse, Pw=10ms

●Packaging specifications and hFE

Type	2SC4672
Package	MPT3
hFE	PQ
Marking	DK *
Code	T100
Basic ordering unit (pieces)	1000

* Denotes hFE

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	60	–	–	V	$I_C = 50\mu A$
Collector-emitter breakdown voltage	BV_{CEO}	50	–	–	V	$I_C = 1mA$
Emitter-base breakdown voltage	BV_{EBO}	6	–	–	V	$I_E = 50\mu A$
Collector cutoff current	I_{CBO}	–	–	0.1	μA	$V_{CB} = 60V$
Emitter cutoff current	I_{EBO}	–	–	0.1	μA	$V_{EB} = 5V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	–	0.1	0.35	V	$I_C/I_B = 1A/50mA$ *
DC current transfer ratio	h_{FE}	82	–	270	–	$V_{CE} = 2V, I_C = 0.5A$ *
Transition frequency	f_T	–	210	–	MHz	$V_{CE} = 2V, I_E = -0.5A, f = 100MHz$
Output capacitance	C_{ob}	–	25	–	pF	$V_{CB} = 10V, I_E = 0A, f = 1MHz$

*Measured using pulse current.

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